

MA3X788

Silicon epitaxial planar type

For super-high speed switching circuit

For small current rectification

Features

- Allowing to rectify under ($I_{F(AV)} = 200$ mA) condition
- Reverse voltage V_R (DC value) = 60 V guaranteed

Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

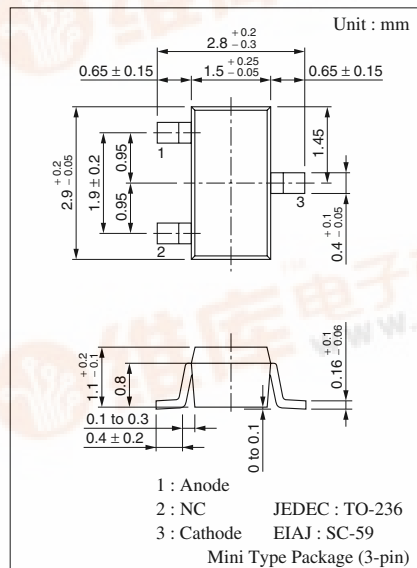
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	60	V
Repetitive peak reverse voltage	V_{RRM}	60	V
Peak forward current	I_{FM}	300	mA
Average forward current	$I_{F(AV)}$	200	mA
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note) *: The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

Electrical Characteristics $T_a = 25^\circ\text{C}$

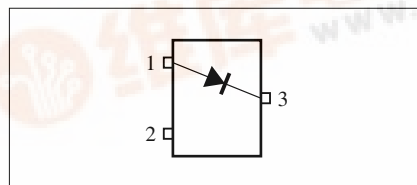
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 50$ V			50	μA
Forward voltage (DC)	V_F	$I_F = 200$ mA			0.65	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		30		pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 100$ mA $I_{rr} = 10$ mA, $R_L = 100 \Omega$		3		ns

- Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.
2. Rated input/output frequency: 1 000 MHz
3. *: t_{rr} measuring circuit



Marking Symbol: M3V

Internal Connection



Bias Application Unit N-50BU

